Operational Amplifier, Rail-to-Rail, 3.5 MHz, Wide Supply

The NCS2004 operational amplifier provides rail-to-rail output operation. The output can swing within 70 mV to the positive rail and 30 mV to the negative rail. This rail-to-rail operation enables the user to make optimal use of the entire supply voltage range while taking advantage of 3.5 MHz bandwidth. The NCS2004 can operate on supply voltage as low as 2.5 V over the temperature range of -40° C to 125°C. The high bandwidth provides a slew rate of 2.4 V/µs while only consuming a typical 390 µA of quiescent current. Likewise the NCS2004 can run on a supply voltage as high as 16 V making it ideal for a broad range of battery operated applications. Since this is a CMOS device it has high input impedance and low bias currents making it ideal for interfacing to a wide variety of signal sensors. In addition it comes in either a small SC–88A or UDFN package allowing for use in high density PCB's.

Features

- Rail-To-Rail Output
- Wide Bandwidth: 3.5 MHz
- High Slew Rate: 2.4 V/µs
- Wide Power Supply Range: 2.5 V to 16 V
- Low Supply Current: 390 μA
- Low Input Bias Current: 45 pA
- Wide Temperature Range: -40°C to 125°C
- Small Packages: 5–Pin SC–88A and UDFN6 1.6x1.6
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

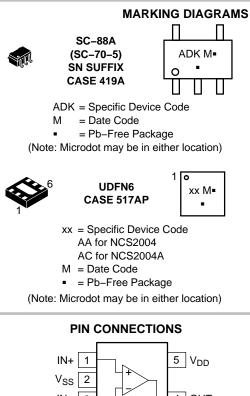
Applications

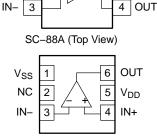
- Notebook Computers
- Portable Instruments



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UDFN (Top View)

ORDERING INFORMATION

Device	Package	Shipping [†]
NCS2004SQ3T2G	SC-88A (Pb-Free)	3000 / Tape & Reel
NCS2004MUTAG, NCS2004AMUTAG	UDFN6 (Pb–Free)	3000 / Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _{DD}	Supply Voltage	16.5	V
V _{ID}	Input Differential Voltage	± Supply Voltage	V
VI	Input Common Mode Voltage Range	-0.2 V to (V _{DD} + 0.2 V)	V
I _I	Maximum Input Current	±10	mA
Ι _Ο	Output Current Range	±100	mA
	Continuous Total Power Dissipation (Note 1)	200	mW
TJ	Maximum Junction Temperature	150	°C
θ_{JA}	Thermal Resistance	333	°C/W
T _{stg}	Operating Temperature Range (free-air)	-40 to 125	°C
T _{stg}	Storage Temperature	-65 to 150	°C
	Mounting Temperature (Infrared or Convection – 20 sec)	260	°C
V _{ESD}	Machine Model Human Body Model	300 2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Continuous short circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V+ or V- will adversely affect reliability.

DC ELECTRICAL CHARACTERISTICS (V_{DD} = 2.5 V, 3.3 V, 5 V and ± 5 V, T_A = 25°C, R_L \geq 10 k Ω unless otherwise noted)

Parameter	Symbol	Conditions		Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	VIC = $V_{DD}/2$, $V_O = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$, R_S	= 50 Ω		0.5	5.0	mV
(NCS2004)		$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$				7.0	
Input Offset Voltage	V _{IO}	$VIC=V_{DD}/2,V_{O}=V_{DD}/2,R_{L}=10\;k\Omega,R_{S}=50\;\Omega$				3.0	mV
(NCS2004A)		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$				5.0	
Offset Voltage Drift	ICV _{OS}	VIC = V _{DD} /2, V _O = V _{DD} /2, R _L = 10 kΩ, R _S = 50 Ω			2.0		μV/°C
Common Mode	CMRR	0 V \leq VIC \leq V_{DD} – 1.35 V, R_S = 50 Ω	V _{DD} = 2.5 V	55	94		dB
Rejection Ratio		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		52			
		0 V \leq VIC \leq V_{DD} – 1.35 V, R_S = 50 Ω	$V_{DD} = 5 V$	65	130		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		62			
		0 V \leq VIC \leq V_{DD} – 1.35 V, R_S = 50 Ω	$V_{DD} = \pm 5 V$	69	140		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		66			
Power Supply Rejection Ratio	PSRR	V_{DD} = 2.5 V to 16 V, VIC = $V_{DD}/2$, No Load		70	135		dB
Rejection Ratio		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		65			
Large Signal Voltage Gain	A _{VD}	$V_{O(pp)} = V_{DD}/2, R_L = 10 \text{ k}\Omega$	V _{DD} = 2.5 V	90	130		dB
voltage Gain		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		76			
		$V_{O(pp)} = V_{DD}/2, R_L = 10 \text{ k}\Omega$	V _{DD} = 3.3 V	92	123		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		76			
		$V_{O(pp)} = V_{DD}/2, R_L = 10 \text{ k}\Omega$	$V_{DD} = 5 V$	95	127		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		86			
		$V_{O(pp)} = V_{DD}/2, R_L = 10 \text{ k}\Omega$	$V_{DD} = \pm 5 V$	95	130		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		90			

Parameter Sym		Conditions		Min	Тур	Max	Unit
Input Bias Current	I _B	$V_{DD} = 5 V, VIC = V_{DD}/2, V_{O} = V_{DD}/2,$	$T_A = 25^{\circ}C$		45	150	pА
		R _S = 50 Ω	T _A = 125°C			1000	
Input Offset Current	I _{IO}	$V_{DD} = 5 V, VIC = V_{DD}/2, V_{O} = V_{DD}/2,$	$T_A = 25^{\circ}C$		45	150	pА
		R _S = 50 Ω	T _A = 125°C			1000	
Differential Input Resistance	r _{i(d)}				1000		GΩ
Common-mode Input Capacitance	C _{IC}	f = 21 kHz			8.0		pF
Output Swing	V _{OH}	$VIC = V_{DD}/2$, $I_{OH} = -1$ mA	V _{DD} = 2.5 V	2.35	2.43		V
(High–level)		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		2.28			
		$VIC = V_{DD}/2$, $I_{OH} = -1$ mA	V _{DD} = 3.3 V	3.15	3.21		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		3.00			
		$VIC = V_{DD}/2$, $I_{OH} = -1$ mA	V _{DD} = 5 V	4.8	4.93		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		4.75			
		$VIC = V_{DD}/2$, $I_{OH} = -1$ mA	$V_{DD} = \pm 5 V$	4.92	4.96		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		4.9			
		$VIC = V_{DD}/2$, $I_{OH} = -5$ mA	V _{DD} = 2.5 V	1.7	2.14		V
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		1.5			
		$VIC = V_{DD}/2$, $I_{OH} = -5$ mA	V _{DD} = 3.3 V	2.5	2.89		
		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		2.1			
		$VIC = V_{DD}/2$, $I_{OH} = -5$ mA	V _{DD} = 5 V	4.5	4.68		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		4.35			
		$VIC = V_{DD}/2$, $I_{OH} = -5$ mA	$V_{DD} = \pm 5 V$	4.7	4.78		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		4.65			
Output Swing	V _{OL}	$VIC = V_{DD}/2$, $I_{OL} = -1$ mA	V _{DD} = 2.5 V		0.03	0.15	V
(Low-level)		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$				0.22	
		$VIC = V_{DD}/2$, $I_{OL} = -1$ mA	V _{DD} = 3.3 V		0.03	0.15	
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$				0.22	
		$VIC = V_{DD}/2$, $I_{OL} = -1$ mA	V _{DD} = 5 V		0.03	0.1	
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$				0.15	
		$VIC = V_{DD}/2$, $I_{OL} = -1$ mA	$V_{DD} = \pm 5 V$		0.05	0.08	
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$				0.1	
		$VIC = V_{DD}/2$, $I_{OL} = -5$ mA	V _{DD} = 2.5 V		0.15	0.7	V
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$				1.1	
		$VIC = V_{DD}/2$, $I_{OL} = -5 \text{ mA}$	V _{DD} = 3.3 V		0.13	0.7	
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$	7			1.1	
		$VIC = V_{DD}/2$, $I_{OL} = -5$ mA	V _{DD} = 5 V		0.13	0.4	
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$	7			0.5	
		$VIC = V_{DD}/2$, $I_{OL} = -5$ mA	$V_{DD} = \pm 5 V$		0.16	0.3	
		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$	1			0.35	

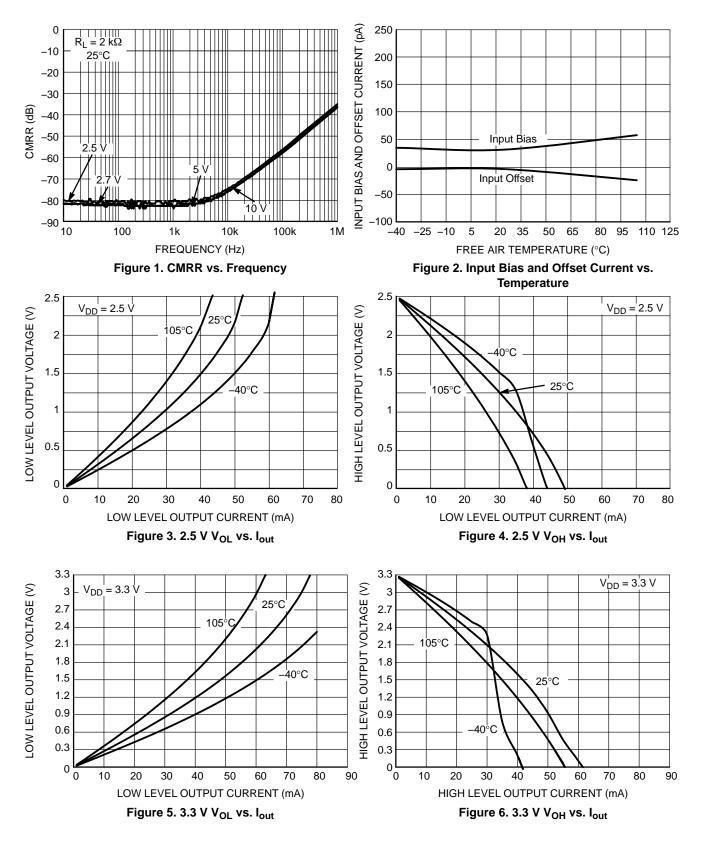
DC ELECTRICAL CHARACTERISTICS (V_{DD} = 2.5 V, 3.3 V, 5 V and ± 5 V, T_A = 25°C, R_L \geq 10 k Ω unless otherwise noted)

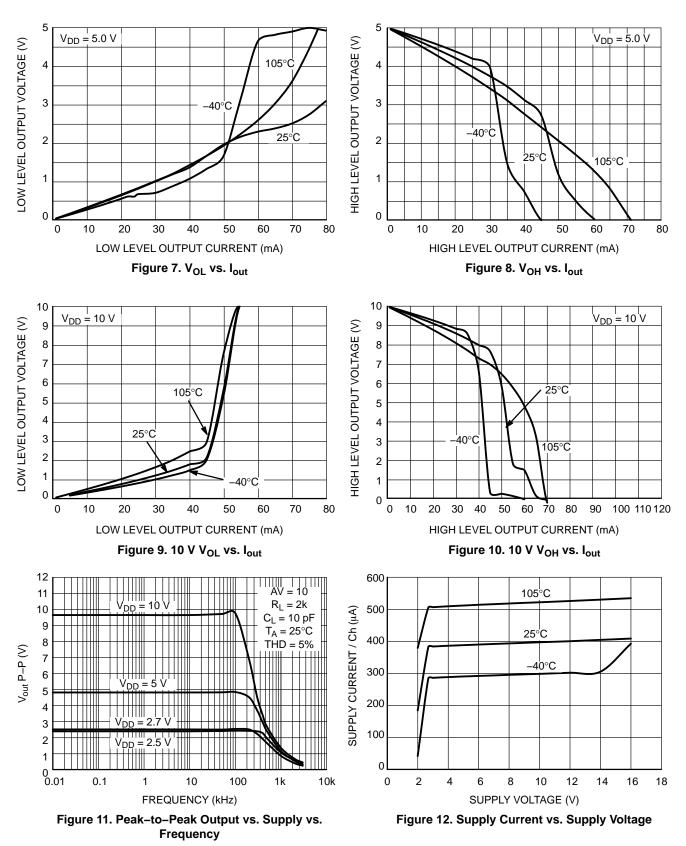
Parameter	Symbol	Conditions	Conditions		Тур	Max	Unit
Output Current	Ι _Ο	V_{O} = 0.5 V from rail, V_{DD} = 2.5 V	Positive rail		4.0		mA
			Negative rail		5.0		
		$V_{O} = 0.5 \text{ V}$ from rail, $V_{DD} = 5 \text{ V}$	Positive rail		7.0		
			Negative rail		8.0		
		$V_{O} = 0.5 \text{ V}$ from rail, $V_{DD} = 10 \text{ V}$	Positive rail		13		
			Negative rail		12		
Power Supply	I _{DD}	$V_{O} = V_{DD}/2$	V _{DD} = 2.5 V		380	560	μA
Quiescent Current			V _{DD} = 3.3 V		385	620	
			V _{DD} = 5 V		390	660	
			V _{DD} = 10 V		400	800	
		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$				1000	

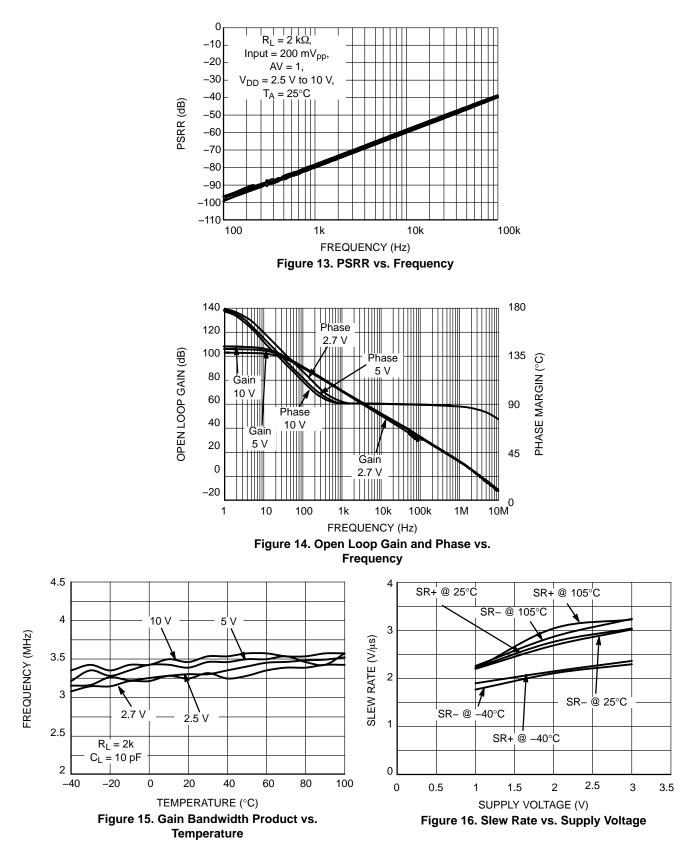
DC ELECTRICAL CHARACTERISTICS (V_{DD} = 2.5 V, 3.3 V, 5 V and \pm 5 V, T_A = 25°C, R_L ≥ 10 k Ω unless otherwise noted)

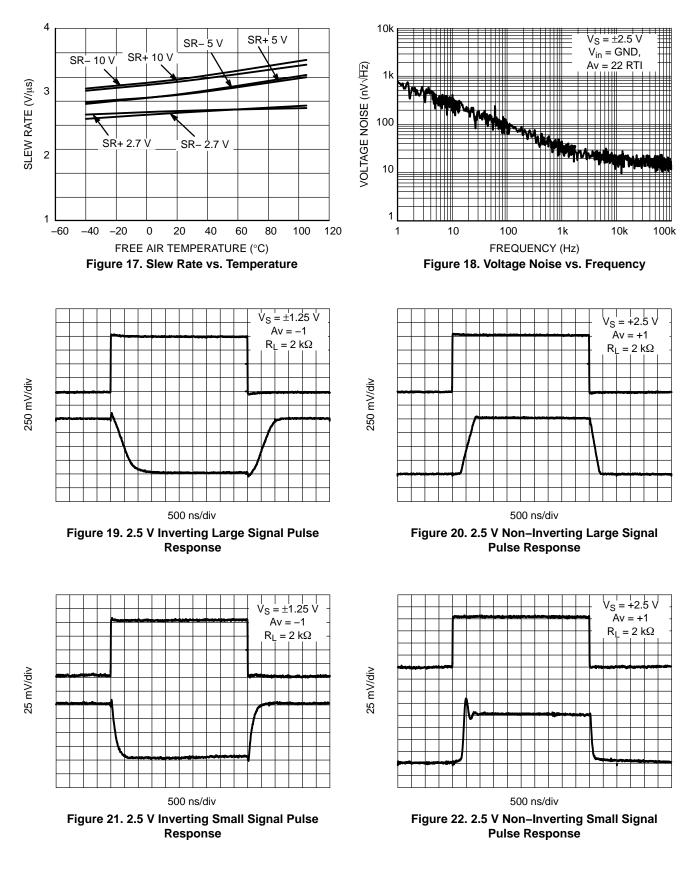
AC ELECTRICAL CHARACTERISTICS (V_{DD} = 2.5 V, 5 V, & \pm 5 V, T_A = 25°C, and R_L \geq 10 k Ω unless otherwise noted)

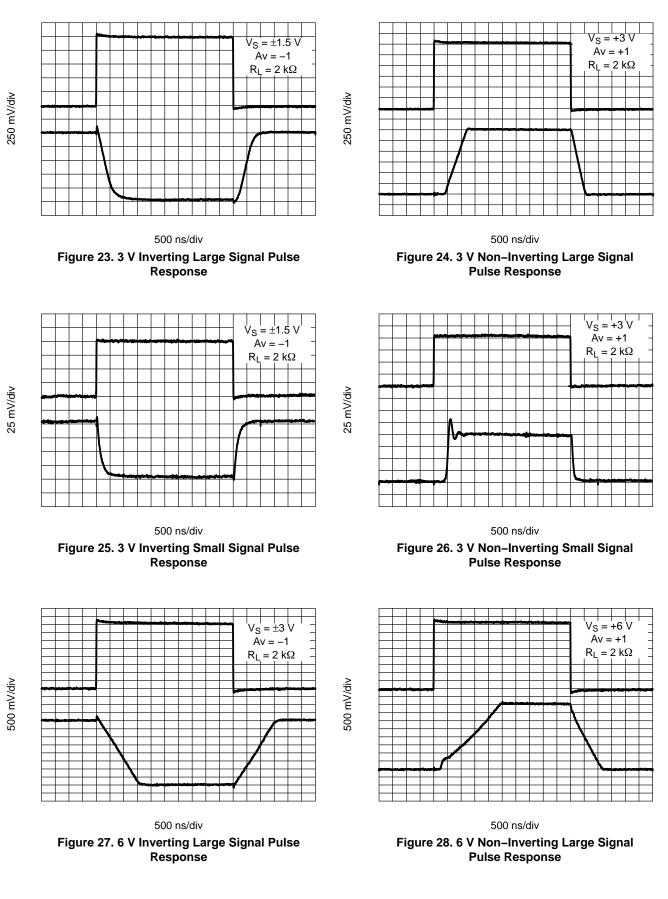
Parameter	Symbol	Conditions		Min	Тур	Мах	Unit
Unity Gain Bandwidth	UGBW	$R_L = 2 k\Omega$, $C_L = 10 pF$	V _{DD} = 2.5 V		3.2		MHz
Danuwiuun			V _{DD} = 5 V to 10 V		3.5		
Slew Rate at Unity Gain	SR	$V_{O(pp)} = V_{DD}/2, R_{L} = 10 \text{ k}\Omega, C_{L} = 50 \text{ pF}$	V _{DD} = 2.5 V	1.35	2.0		V/μS
		$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$		1			
		$V_{O(pp)} = V_{DD}/2, R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF}$	$V_{DD} = 5 V$	1.45	2.3		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		1.2			
		$V_{O(pp)} = V_{DD}/2, R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF}$	$V_{DD} = \pm 5 V$	1.8	2.6		
		$T_A = -40^{\circ}C$ to $+125^{\circ}C$		1.3			
Phase Margin	θ_{m}	$R_L = 2 k\Omega, C_L = 10 pF$			45		0
Gain Margin		$R_L = 2 k\Omega$, $C_L = 10 pF$			14		dB
Settling Time to 0.1%	t _S	V-step(pp) = 1 V, AV = -1, R _L = 2 k Ω , C _L = 10 pF	V _{DD} = 2.5 V		2.9		μS
			V-step(pp) = 1 V, AV = -1, R _L = 2 k Ω , C _L = 68 pF	V _{DD} = 5 V, ±5 V		2.0	
Total Harmonic	THD+N		AV = 1		0.004		%
Distortion plus Noise		f = 10 kHz	AV = 10		0.04		
			AV = 100		0.3		
		$V_{DD} = 5 V, \pm 5 V, V_{O(pp)} = V_{DD}/2,$	AV = 1		0.004		
		$R_L = 2 k\Omega$, f = 10 kHz ^(rr)	AV = 10		0.04		
			AV = 100		0.03		
Input–Referred	e _n	f = 1 kHz	_		30		nV/√Hz
Voltage Noise		f = 10 kHz			20]
Input–Referred Current Noise	i _n	f = 1 kHz			0.6		fA/√Hz



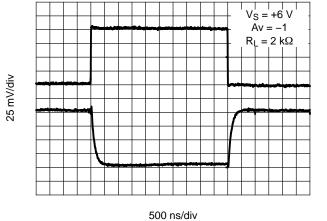


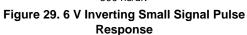






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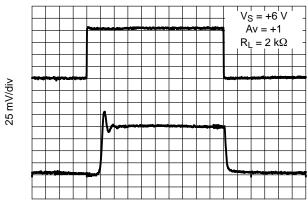
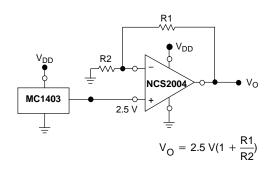


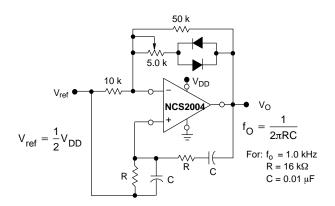


Figure 30. 6 V Non–Inverting Small Signal Pulse Response

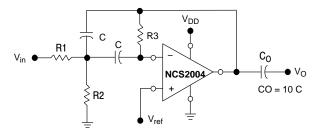
APPLICATIONS











R2 Hysteresis VOH R1 Vo Vref 4 NCS2004 Vo Vin (VOL VinL VinH V_{ref} $V_{in}L = \frac{R1}{R1 + R2} \quad (V_{OL} - V_{ref}) + V_{ref}$
$$\begin{split} V_{in}H &= \frac{R1}{R1+R2} \quad (V_{OH}-V_{ref})+V_{ref} \\ H &= \frac{R1}{R1+R2} \quad (V_{OH}-V_{OL}) \end{split}$$

Figure 33. Comparator with Hysteresis

Given: f_0 = center frequency A(f_0) = gain at center frequency

Choose value f_o, C_Q
Then: R3 =
$$\frac{Q}{\pi f_0 C}$$

R1 = $\frac{R3}{2 A(f_0)}$
R2 = $\frac{R1 R3}{4Q^2 R1 - R3}$

For less than 10% error from operational amplifier, ((Q_O f_O)/BW) < 0.1 where f_o and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 34. Multiple Feedback Bandpass Filter

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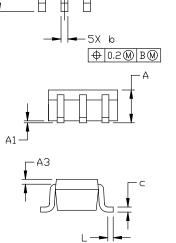


SCALE 2:1

SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE M**

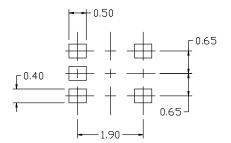
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 419A-01 DBSOLETE, NEW STANDARD 419A-02 З.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



e

F1



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS				
ויונע	MIN.	NDM.	MAX,		
А	0.80	0.95	1.10		
A1			0.10		
A3		0.20 REF	-		
b	0.10	0.20	0.30		
C	0.10		0.25		
D	1.80	2.00	2,20		
E	2.00	2.10	5,20		
E1	1.15	1.25	1.35		
e		0.65 BSI	С		
L	0.10	0.15	0.30		

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

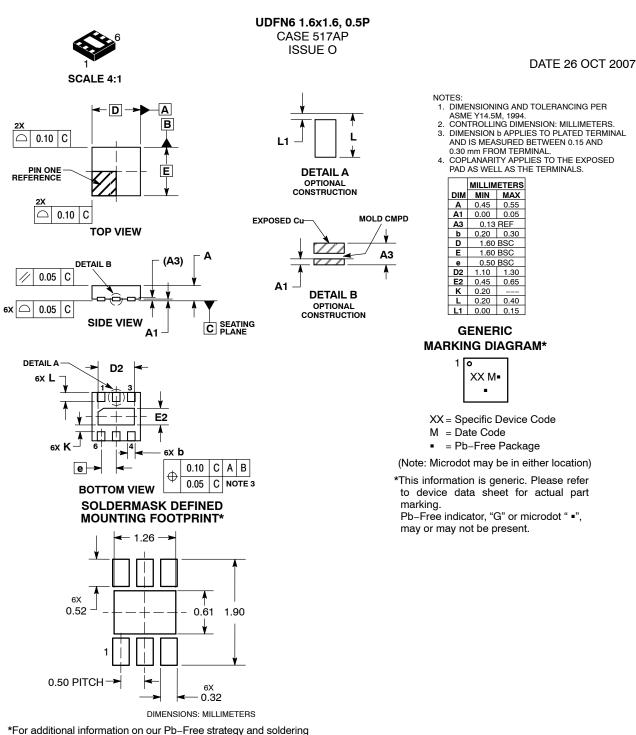
Μ = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	3. BASE 4. COLLECTOR 1 5. COLLECTOR 98ASB42984B		out in the datasheet refer to the de datasheet pinout or pin assignmen of when accessed directly from the Document Re when stamped "CONTROLLED COPY" in red.	nt.
OCUMENT NUMBER:	98ASB42984B			pository.

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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